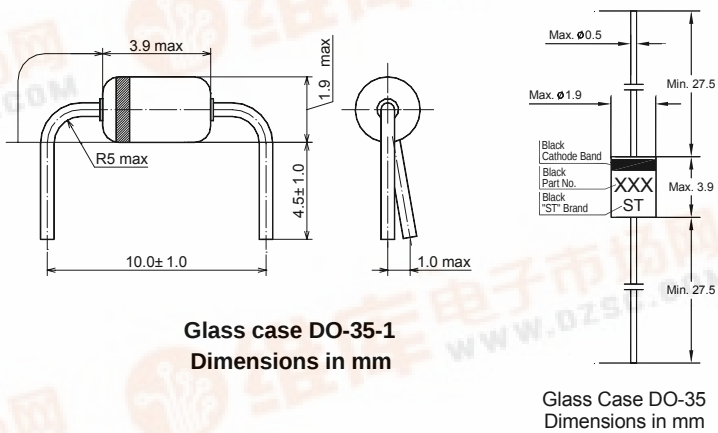


ST60P, ST60S

SILICON SCHOTTKY BARRIER DIODE

Characteristics equivalent to
1N60P and 1N60S

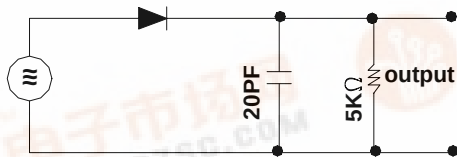


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	20	V
Average Rectified Output Current	I_O	50	mA
Peak Forward Current	I_{FM}	150	mA
Surge Forward Current	I_{surge}	500	mA
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_S	- 55 to + 175	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Forward Current at $V_F = 1\text{ V}$	I_F	4	-	mA
Reverse Current at $V_R = 10\text{ V}$	I_R	-	50 100	μA
Junction Capacitance at $f = 1\text{ MHz}$, $V = -1\text{ V}$	C	-	1	pF
Rectification efficiency at $V_i = 2\text{ Vrms}$, $R = 5\text{ K}\Omega$, $C = 20\text{ pF}$, $f = 40\text{ MHz}$	η	55	-	%



Input 2Vrms
Rectification Efficiency Measurement Circuit

SEMTECH ELECTRONICS LTD.
(Subsidiary of Sino-Tech International Holdings Limited, a company
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